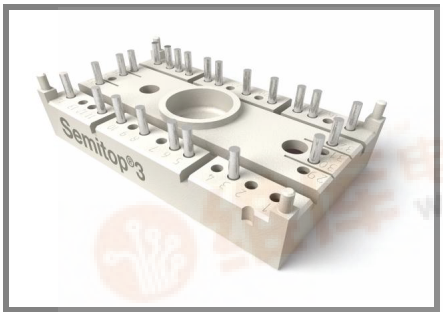
SK50GH065F



SEMITOP® 3

IGBT Module

SK50GH065F

Target Data

Features

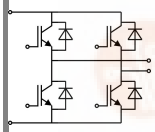
- Compact design
- One screw mounting
- Heat transfer and isolation through direct copper bonding aluminium oxide ceramic (DBC)
- Ultrafast NPT IGBT
- Turbo FWDiodes
- Low treshold voltage
- Low tail current with low temperature dependence

Typical Applications

- Switching (not for linear use)
- Inverter
- Switched mode power supplies
- UPS

Remarks

- V_F = chip level value



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Absolute Maximum Ratings T_s = 25 °C, unless otherwise specified

Symbol	Conditions		Values	Units
IGBT				
V_{CES}	T_j = 25 °C		600	V
I_C	T_j = 125 °C	T_s = 25 °C	54	A
		T_s = 80 °C	40	A
I_{CRM}	I_{CRM}= 2 x I_{Cnom}		100	A
V_{GES}			± 20	V
t_{psc}	V_{CC} = 300 V; V_{GE} ≤ 20 V; V_{CES} < 600 V	T_j = 125 °C	10	µs
Inverse Diode				
I_F	T_j = 150 °C	T_s = 25 °C	82	A
		T_s = 80 °C	50	A
I_{FRM}	I_{FRM}= 2 x I_{Fnom}		120	A
Module				
$I_{t(RMS)}$				A
T_{vj}			-40 ... +150	°C
T_{stg}			-40 ... +125	°C
V_{isol}	AC, 1 min.		2500	V

Characteristics T_s = 25 °C, unless otherwise specified

Symbol	Conditions		min.	typ.	max.	Units
IGBT						
$V_{GE(th)}$	V_{GE} = V_{CE}, I_C = 0,7 mA		3	4	5	V
I_{CES}	V_{GE} = 600 V, V_{CE} = V_{CES}	T_j = 25 °C			0,0022	mA
I_{GES}	V_{CE} = 0 V, V_{GE} = 20 V	T_j = 25 °C			120	nA
V_{CE0}		T_j = 25 °C		1,2	1,3	V
		T_j = 125 °C		1,1	0,9	V
r_{CE}	V_{GE} = 15 V	T_j = 25°C			12	mΩ
		T_j = 125°C			22	mΩ
$V_{CE(sat)}$	I_{Cnom} = 60 A, V_{GE} = 15 V	T_j = 25°C$_{chiplev.}$		2	2,5	V
		T_j = 125°C$_{chiplev.}$		2,2	2,7	V
C_{ies}	V_{CE} = 25, V_{GE} = 0 V	f = 1 MHz		3,2		nF
C_{oes}				0,3		nF
C_{res}				0,18		nF
$t_{d(on)}$	R_{Gon} = 15 Ω	V_{CC} = 300V				ns
t_r		I_{Cnom}= 60A				ns
E_{on}		T_j = 125 °C		1,07		mJ
$t_{d(off)}$	R_{Goff} = 15 Ω	V_{GE}=±15V				ns
t_f						ns
E_{off}				1,76		mJ
$R_{th(j-s)}$	per IGBT				0,85	K/W

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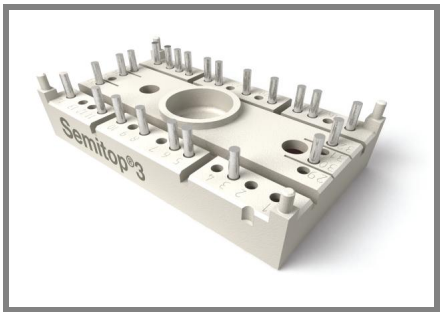

SEMITOP® 3

IGBT Module

SK50GH065F

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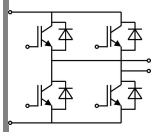

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Characteristics						
Symbol	**Conditions**		**min.**	**typ.**	**max.**	**Units**
Inverse Diode						
$V_F = V_{EC}$	I_{Fnom} = 60 A; V_{GE} = 0 V	T_j = 25 °C$_{chiplev.}$		1,1	1,6	V
		T_j = 125 °C$_{chiplev.}$			1,2	V
V_{F0}		T_j = 150 °C		0,85		V
r_F		T_j = 150 °C		12		mΩ
I_{RRM}	I_{Fnom} = A	T_j = °C				A
Q_{rr}						µC
E_{rr}	V_{CC}=300V					mJ
$R_{th(j-s)D}$	per diode				1,1	K/W
M_s	to heat sink		2,25		2,5	Nm
w				30		g

This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, Chapter IX.

This technical information specifies semiconductor devices but promises no characteristics. No warranty or guarantee expressed or implied is made regarding delivery, performance or suitability.

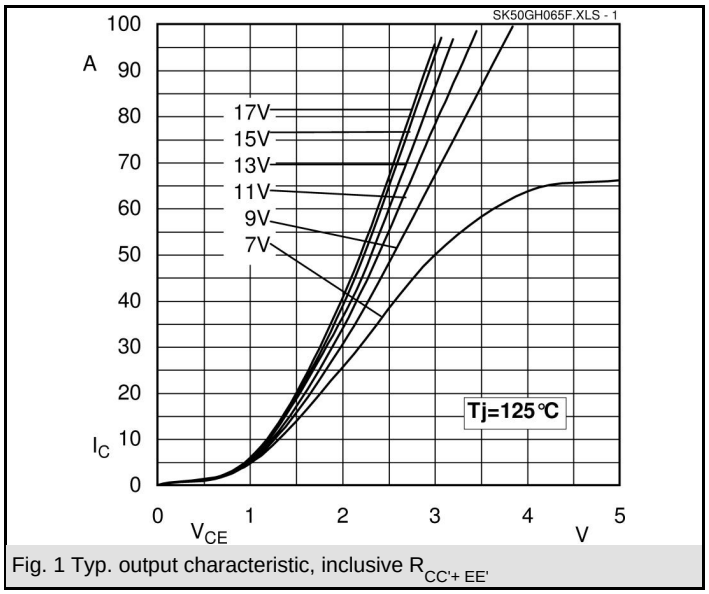

Fig. 1 Typ. output characteristic, inclusive $R_{CC'+EE'}$

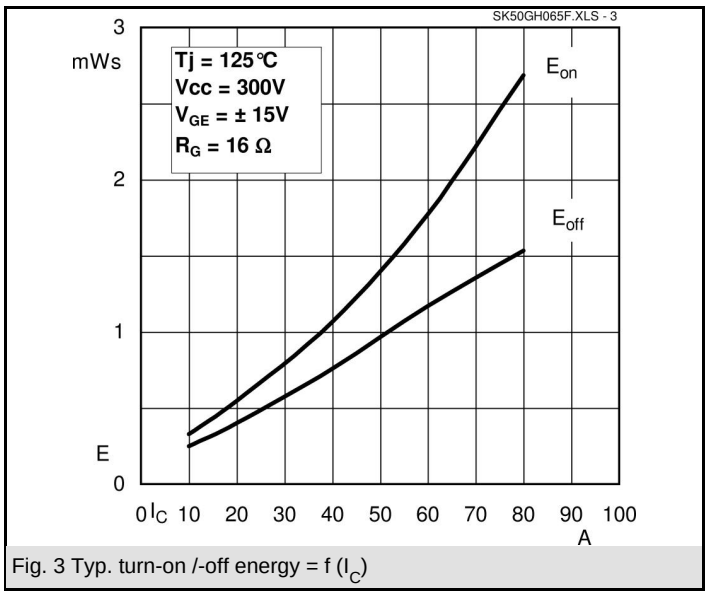

Fig. 3 Typ. turn-on /-off energy = f (I_C)

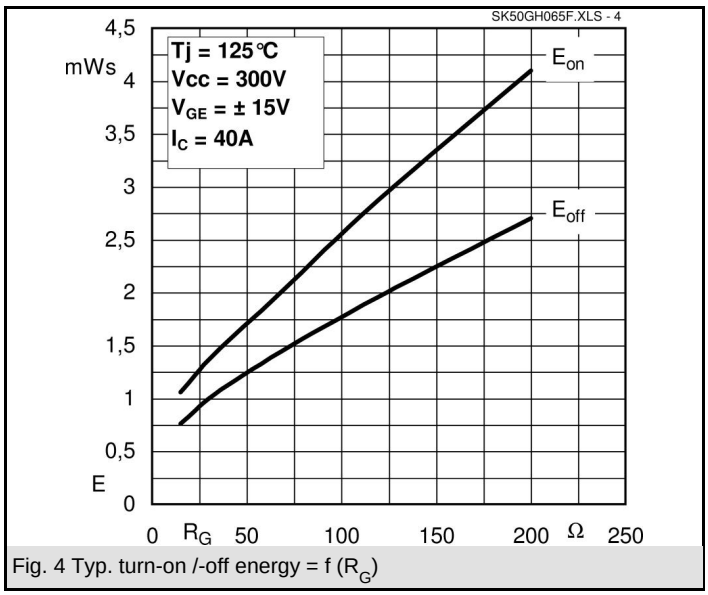

Fig. 4 Typ. turn-on /-off energy = f (R_G)

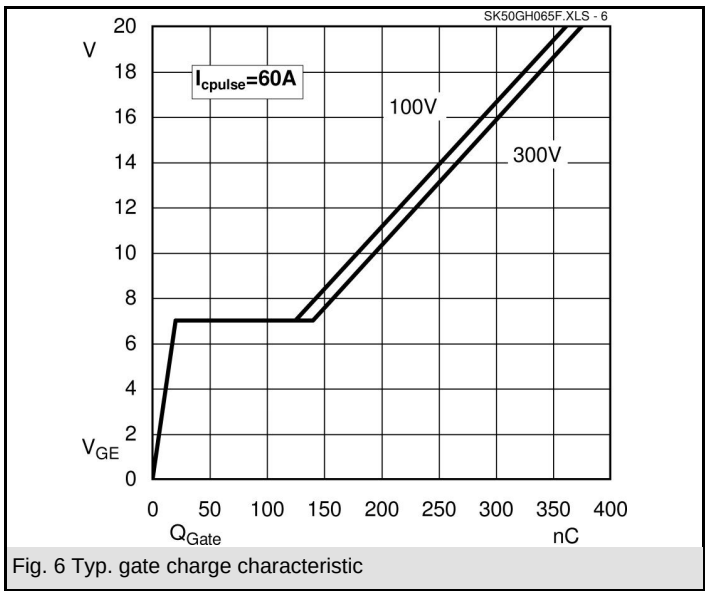

Fig. 6 Typ. gate charge characteristic

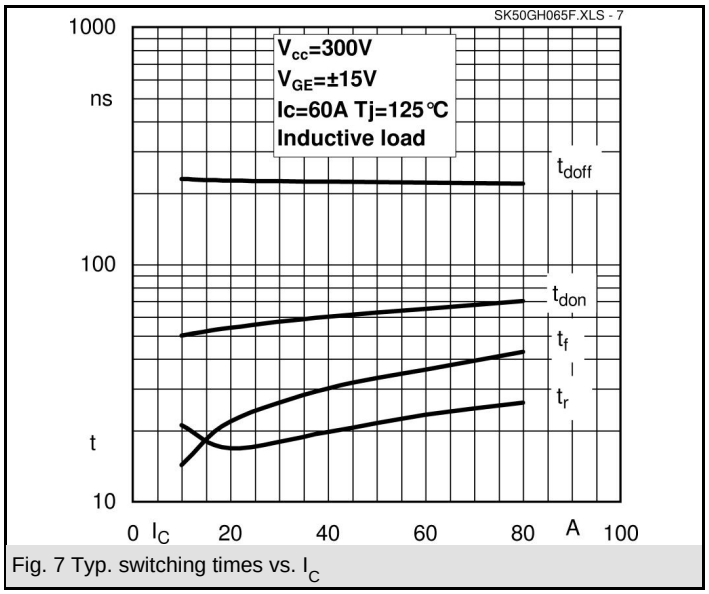

Fig. 7 Typ. switching times vs. I_C

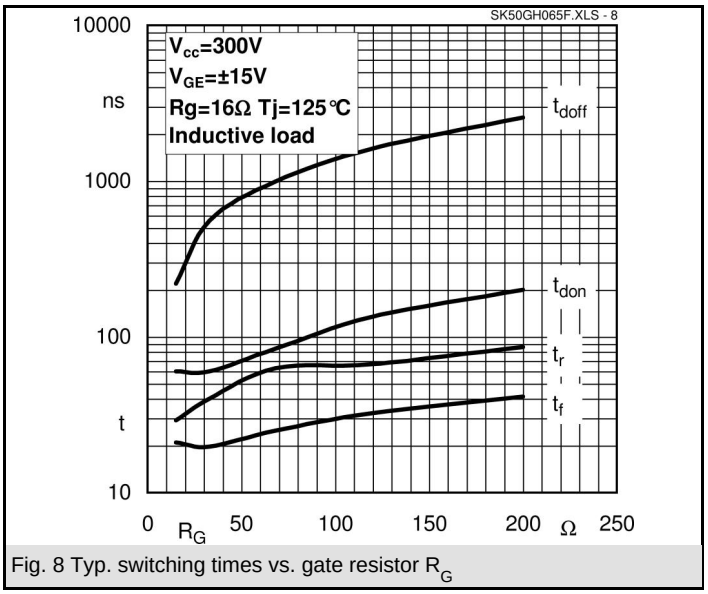

Fig. 8 Typ. switching times vs. gate resistor R_G

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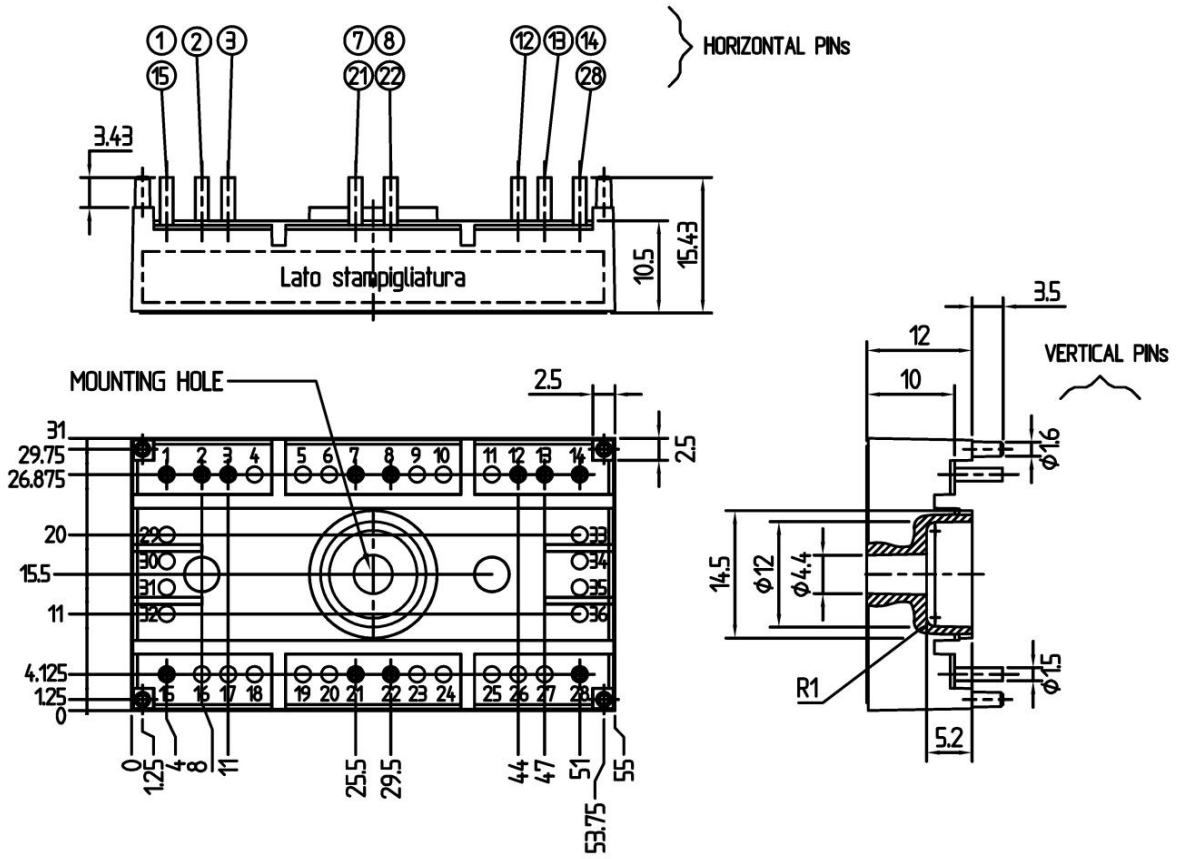
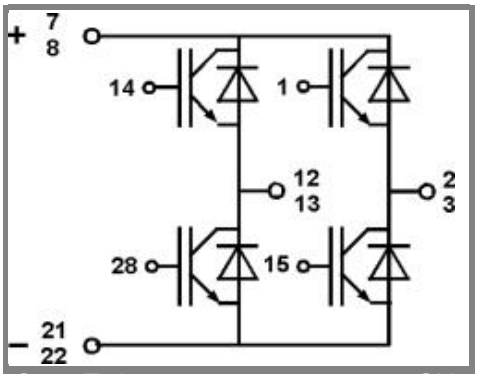
UL recognized file no. E 63 532



Case T19 (Suggested hole diameter, in the PCB, for solder pins and plastic mounting pins: 2mm)



Case T19 GH